FM16P10Q

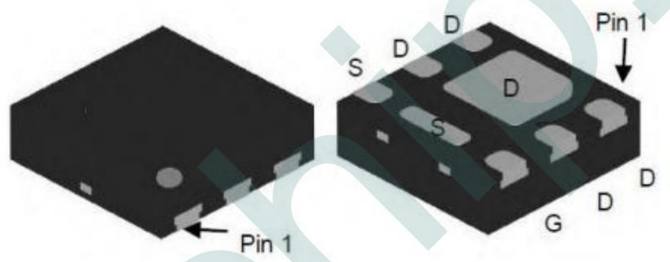
P-Channel Enhancement Mode MOSFET

- VDS=-16V, ID=-16A
- $R_{DS(ON)}$ =11.8mΩ @ V_{GS} = -4.5V
- $R_{DS(ON)}$ =15.6mΩ @ V_{GS} = -2.5V
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current

Application

- LCD TV
- Notebook
- Elevator
- Inductive heating Power tools
- Power tools

Package



DFN-6 2*2

Absolute Maximum Ratings (Tc=25℃ unless otherwise specified)

Symbol	Parameter		Value	Units
V_{DSS}	Drain-Source Voltage		-16	V
V_{GSS}	Gate-Source Voltage		±10	V
I_D	Continuous Drain Current	T_C = 25℃	-16	A
		T_C = 100℃	-7	A
I_{DM}	Pulsed Drain Current note1		32	A
E_{AS}	Single Pulsed Avalanche Energynote2		42	mJ
P_d	Power Dissipation	T_C = 25℃	21	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.17	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	℃

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